

FEATURES

- $R_{DS(ON)}$ 14m Ω @ $V_{GS}=-10V$ (Typ)
- $R_{DS(ON)}$ 16m Ω @ $V_{GS}=-4.5V$ (Typ)
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

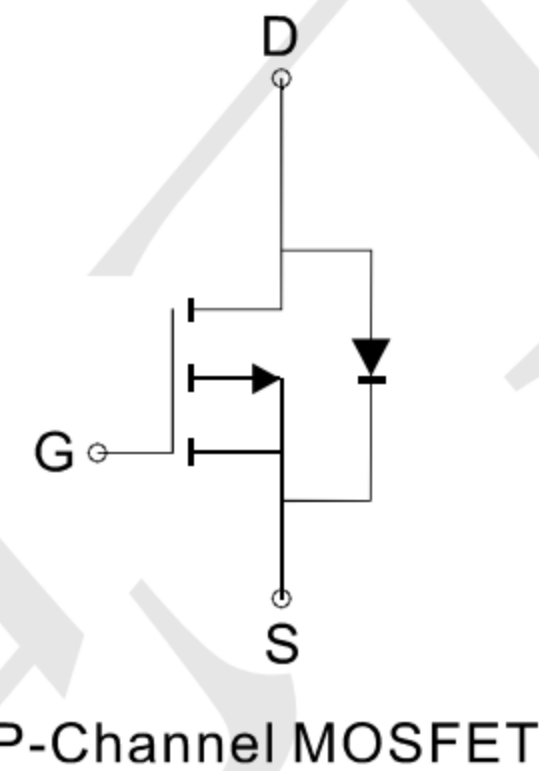
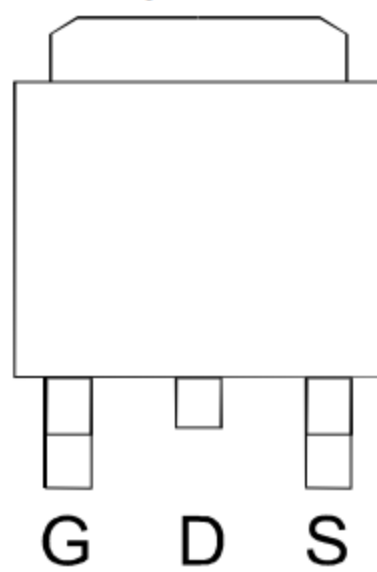
APPLICATIONS

- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter

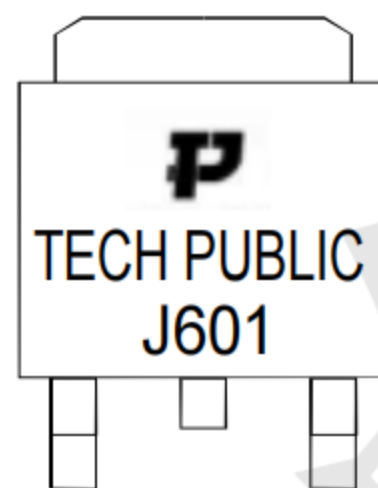
Package and Pin Configuration

(TO-252-3L)

Top View



Marking:



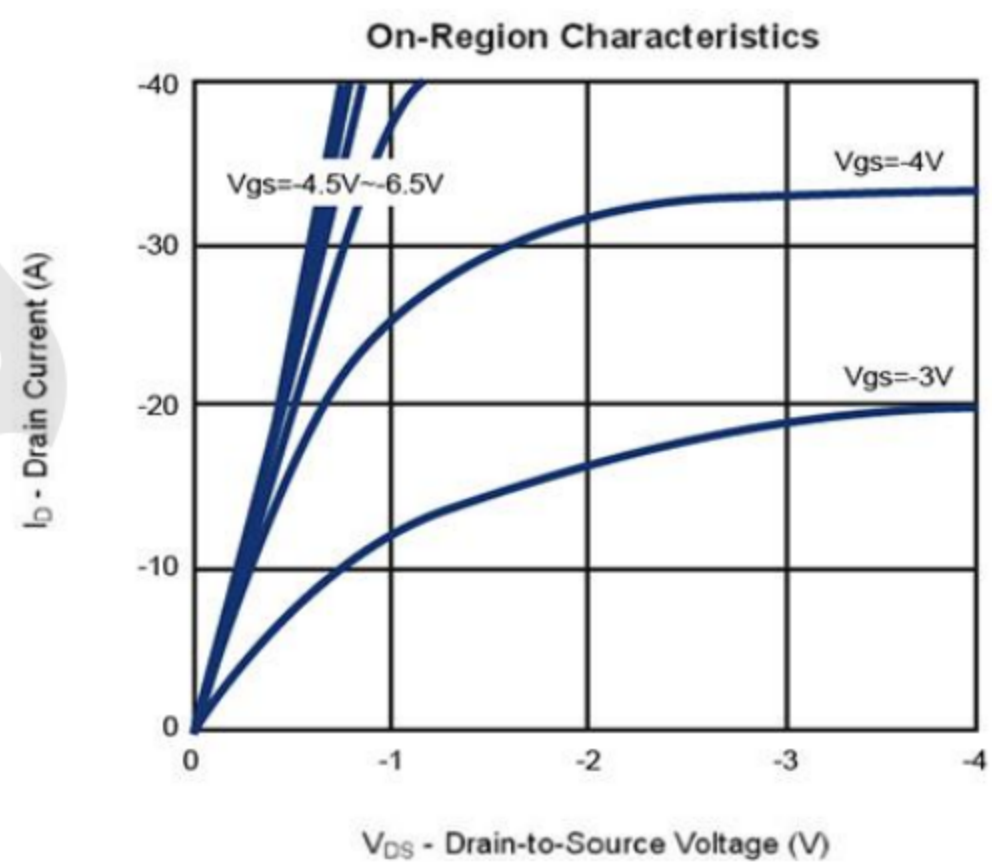
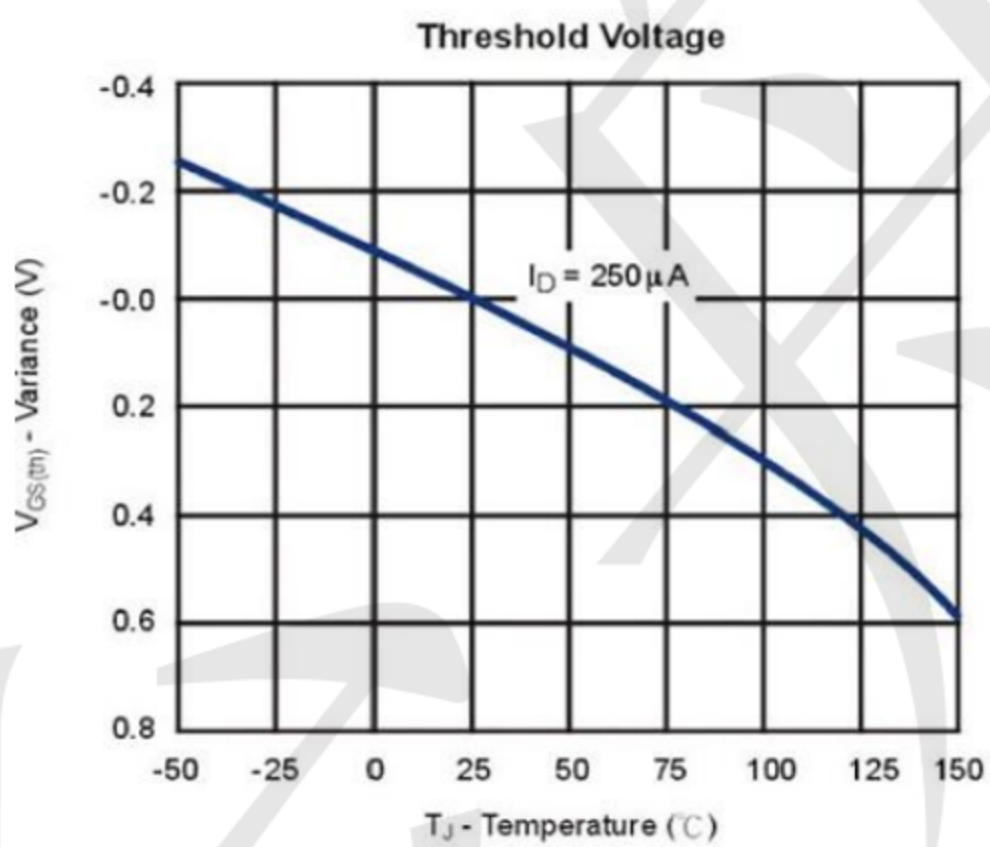
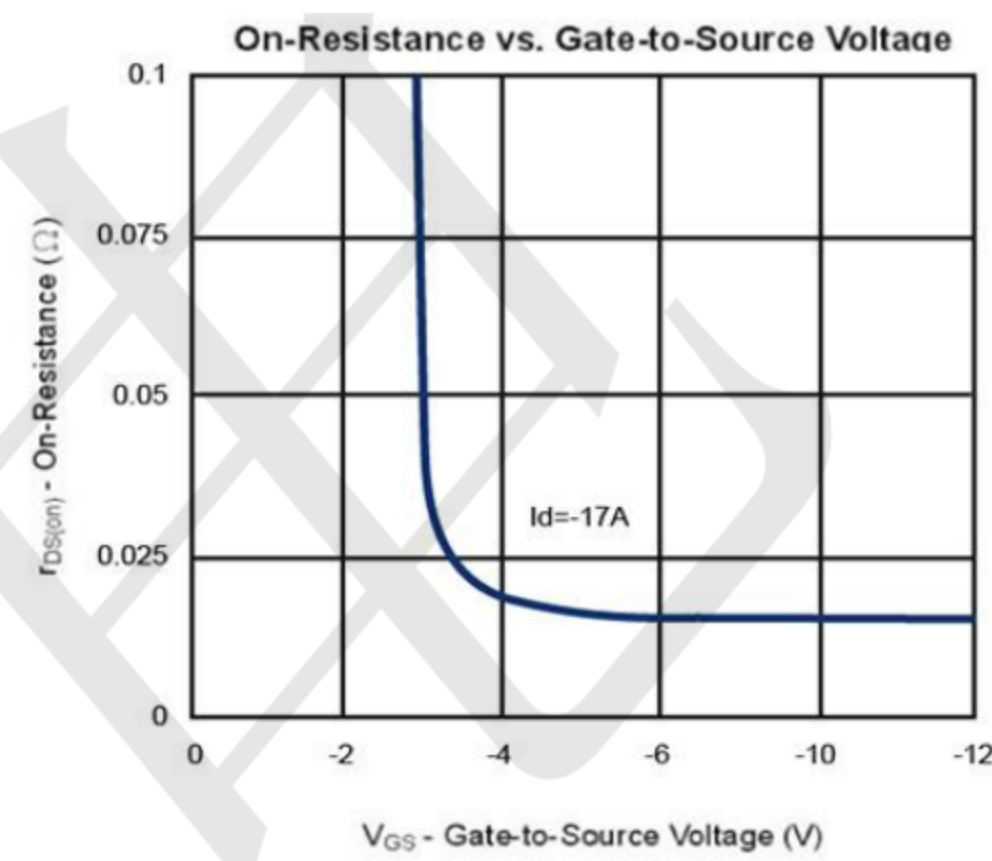
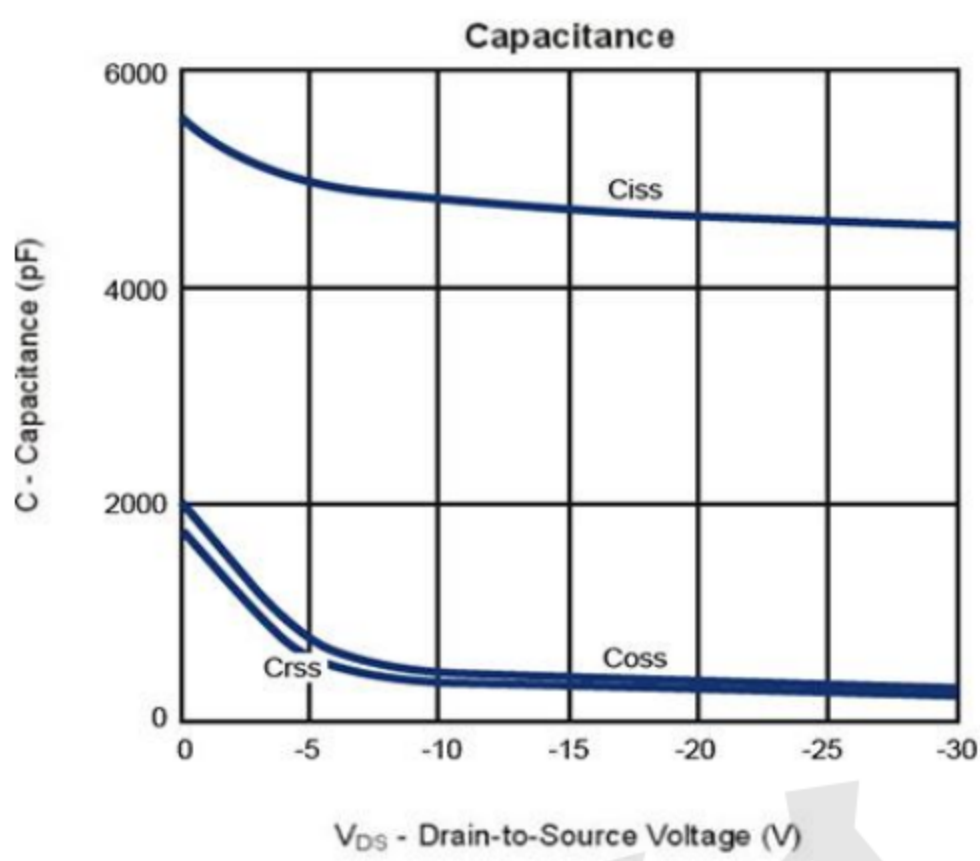
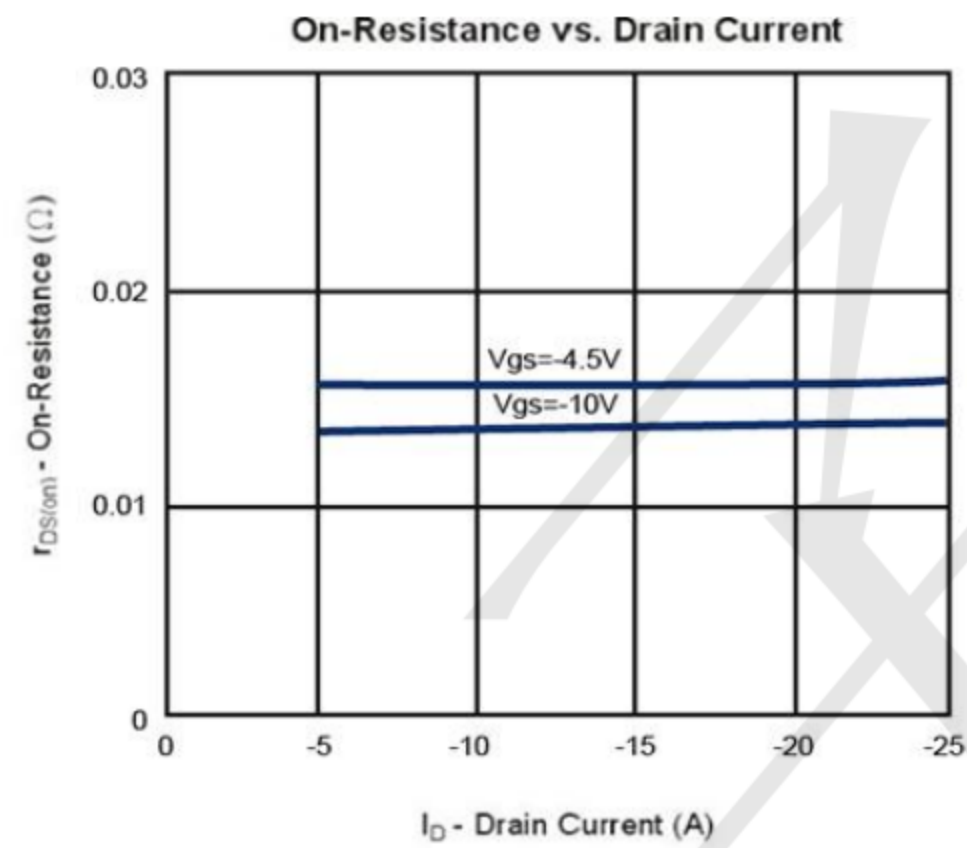
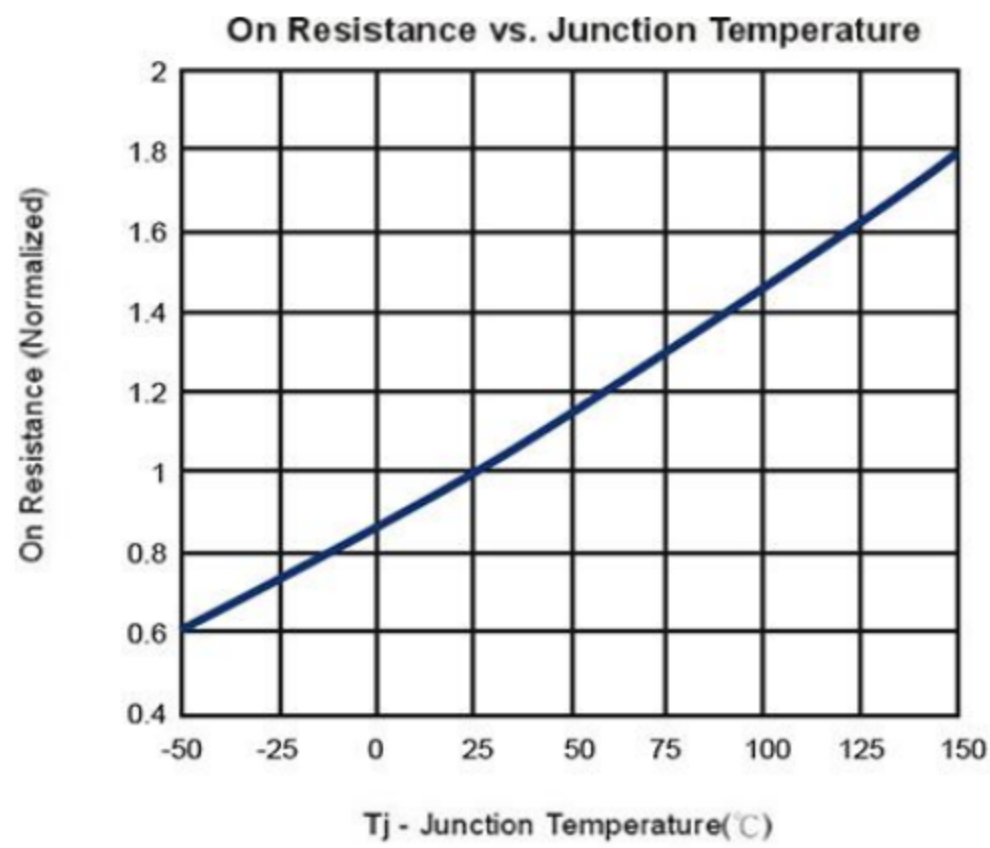
Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

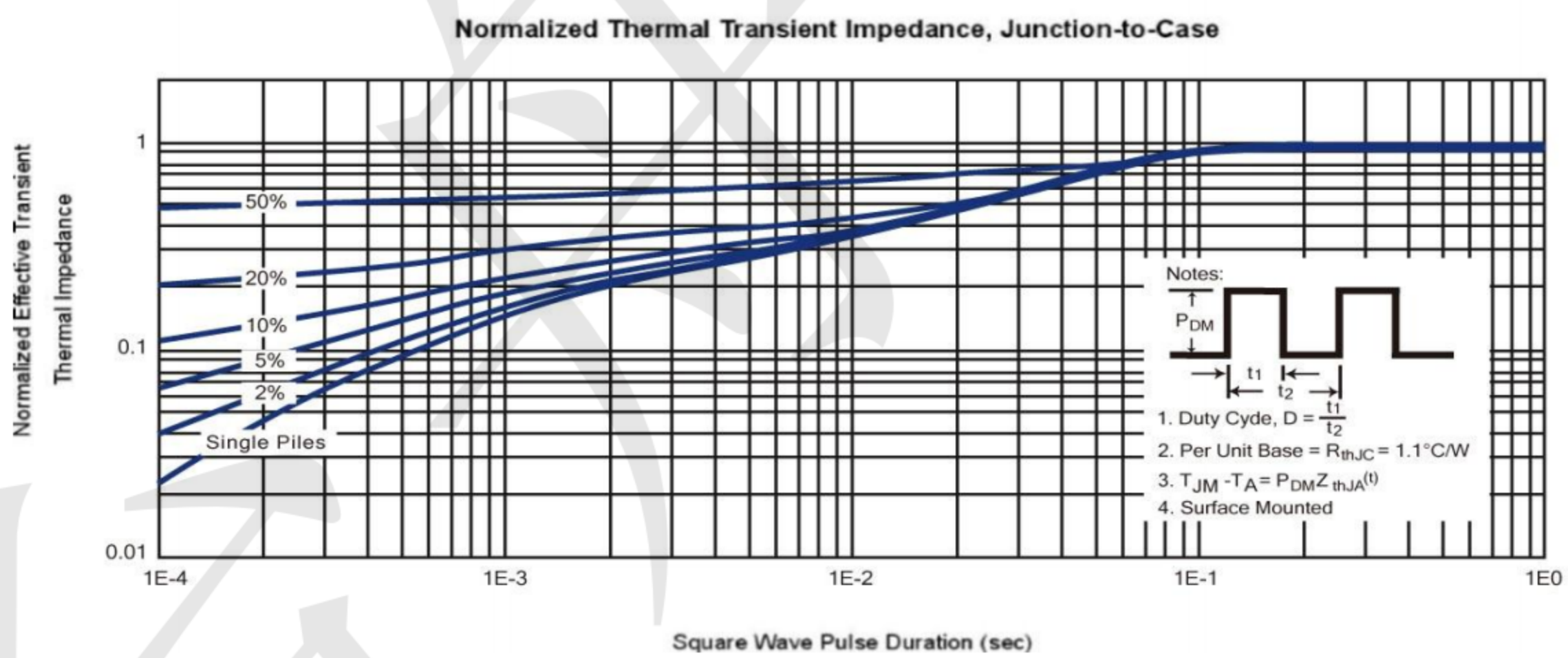
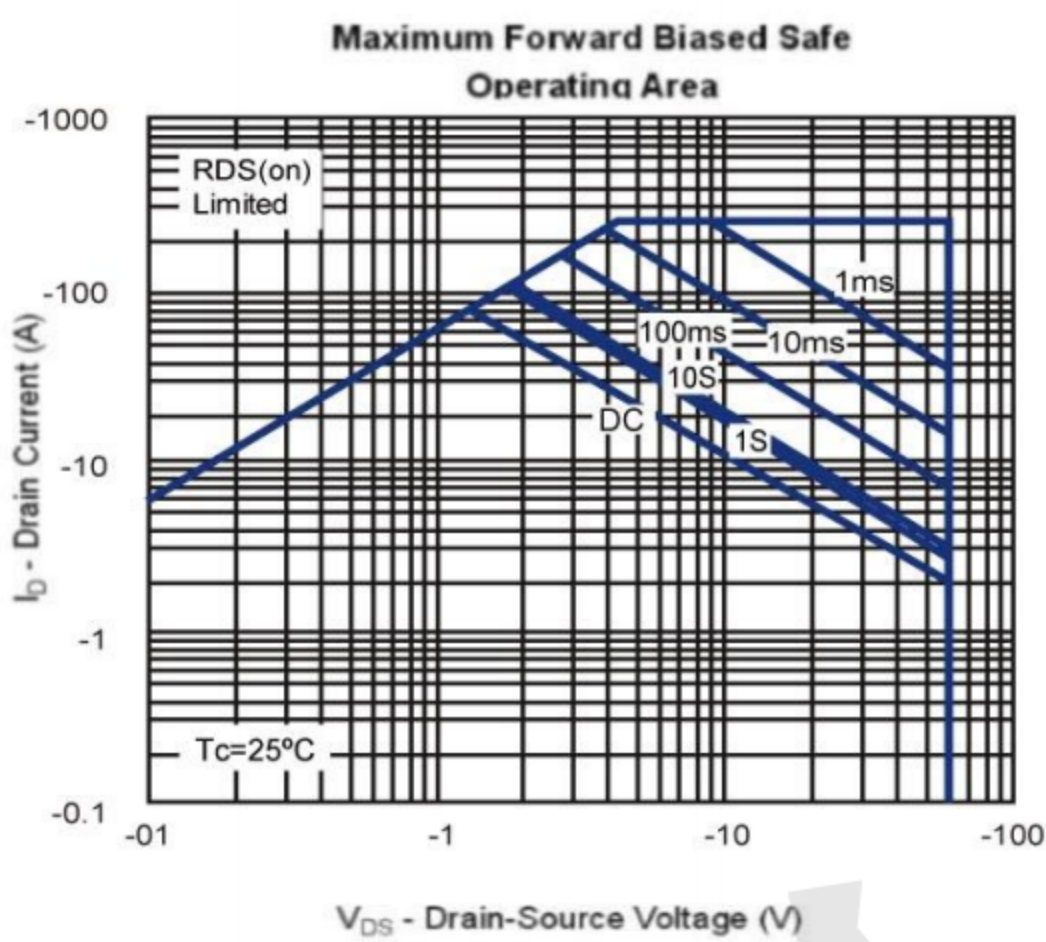
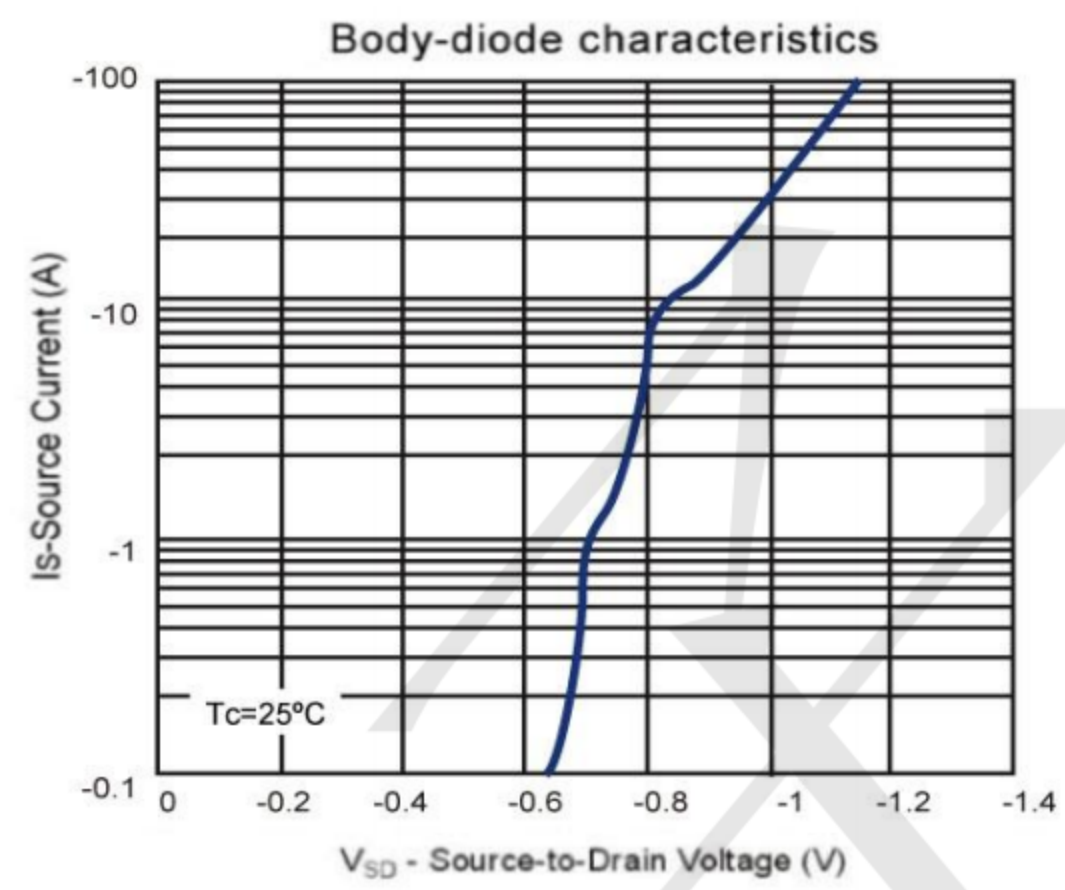
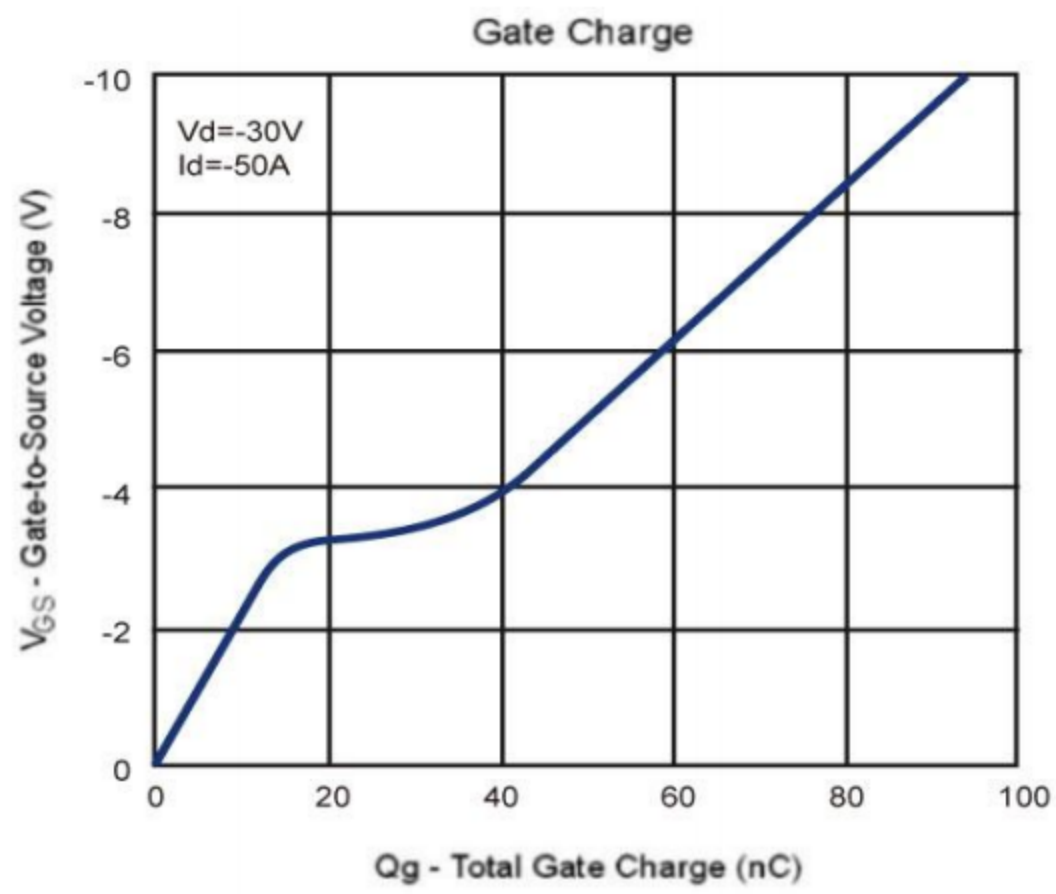
Parameter	Symbol	Maximum Ratings	Unit	
Drain-Source Voltage	V_{DS}	-60	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current*	I_D	$T_C=25^{\circ}C$	-61	A
		$T_C=70^{\circ}C$	-49	
Pulsed Drain Current	I_{DM}	-244	A	
Maximum Power Dissipation*	P_D	$T_C=25^{\circ}C$	114	W
		$T_C=70^{\circ}C$	73	
Operating Junction Temperature	T_J	-55 to 150	$^{\circ}C$	
Thermal Resistance-Junction to Case*	$R_{\theta JC}$	1.1	$^{\circ}C/W$	

Electrical Characteristics (T_j=25°C unless otherwise noted)

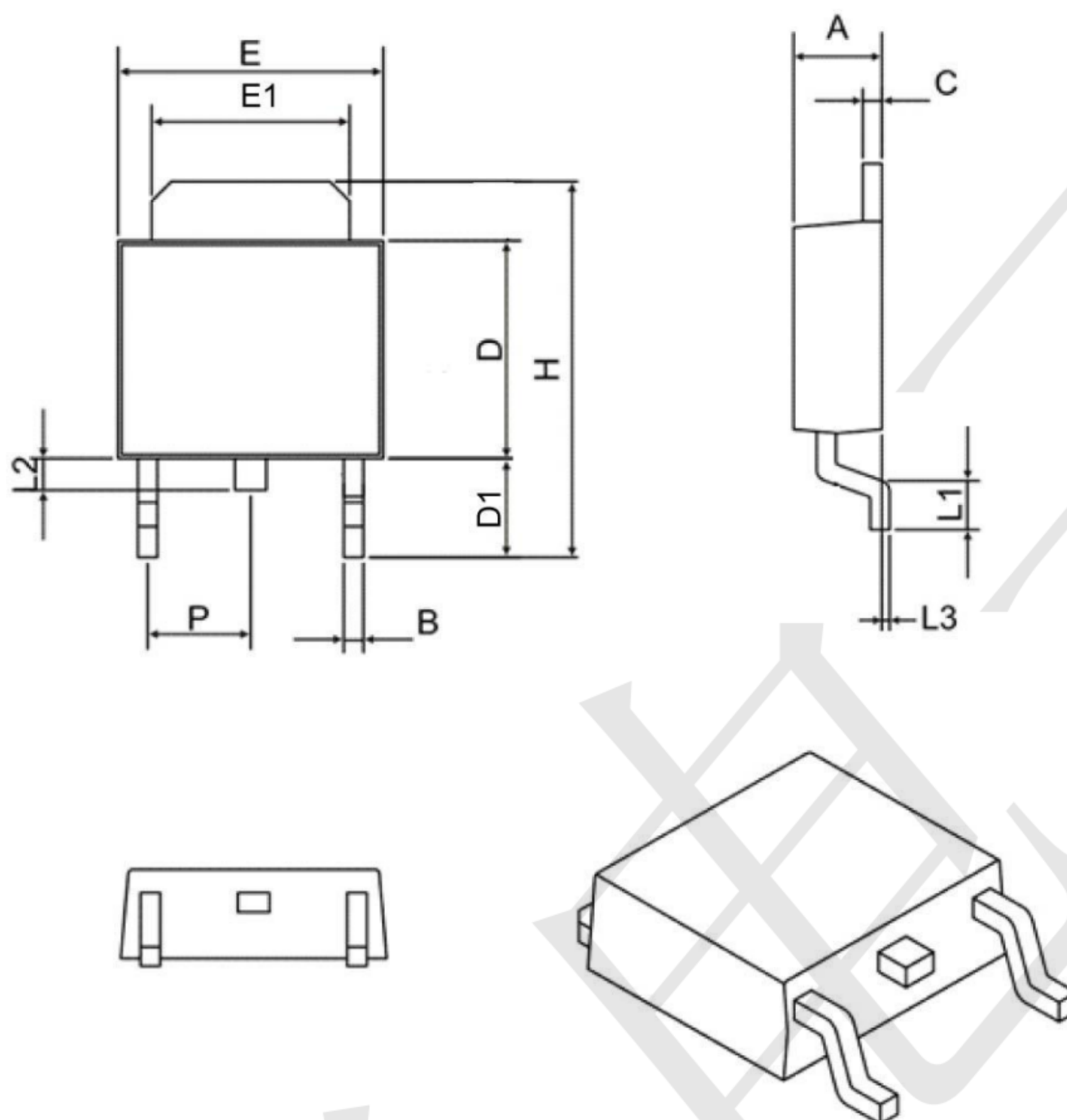
Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μA	-60			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250 μA	-1		-3	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±20V			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-60V, V _{GS} =0V			-1	μA
R _{DS(ON)}	Drain-Source On-State Resistance ^a	V _{GS} =-10V, I _D = -17A		14	17	mΩ
		V _{GS} =-4.5V, I _D = -14A		16	20	
V _{SD}	Diode Forward Voltage	I _S =-17A, V _{GS} =0V		-0.9	-1.2	V
DYNAMIC						
Q _g	Total Gate Charge(10V)	V _{DS} =-30V, V _{GS} =-10V, I _D =-50A		94		nC
Q _g	Total Gate Charge(4.5V)			46		
Q _{gs}	Gate-Source Charge	V _{DS} =-30V, V _{GS} =-4.5V, I _D =-50A		18		
Q _{gd}	Gate-Drain Charge			24		
C _{iss}	Input capacitance			4707		pF
C _{oss}	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, F=1MHz		373		
C _{rss}	Reverse Transfer Capacitance			336		
t _{d(on)}	Turn-On Delay Time			53		ns
t _r	Turn-On Rise Time	V _{DS} =-30V, R _L =30Ω		19		
t _{d(off)}	Turn-Off Delay Time	V _{GEN} =-10V, R _G =6Ω		221		
t _f	Turn-Off Fall Time			61		

Typical Electrical and Thermal Characteristics





TO252-2L Package Information



SYMBOL	MIN	MAX
A	2.10	2.50
B	0.40	0.90
C	0.40	0.90
D	5.30	6.30
D1	2.20	2.90
E	6.30	6.75
E1	4.80	5.50
L1	0.90	1.80
L2	0.50	1.10
L3	0.00	0.20
H	8.90	10.40
P	2.30 BSC	

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [TECH PUBLIC](#) manufacturer:

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [2SK2267\(Q\)](#) [BUK455-60A/B](#) [TK100A10N1,S4X\(S](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#)
[IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [TK31J60W5,S1VQ\(O](#) [TK31J60W,S1VQ\(O](#) [TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#)
[DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)
[DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)
[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1_T0_00201](#) [PJMF380N65E1_T0_00201](#)
[PJMF280N60E1_T0_00201](#) [PJMF600N65E1_T0_00201](#) [PJMF900N65E1_T0_00201](#)